

RF PARAMETERS

The RF calculations performed for the SNS coupler window, using MAFIA and HFSS programs, and analyzed for their multipacting behavior with a program from the University of Helsinki [2] and are identical for this coupler.

Figures 2, 3 and 4 show the results of the HFSS calculations for the E and H field distribution for the window design for 1KW input power. In Figs 3 and 4, the negative side is the air side of the window.

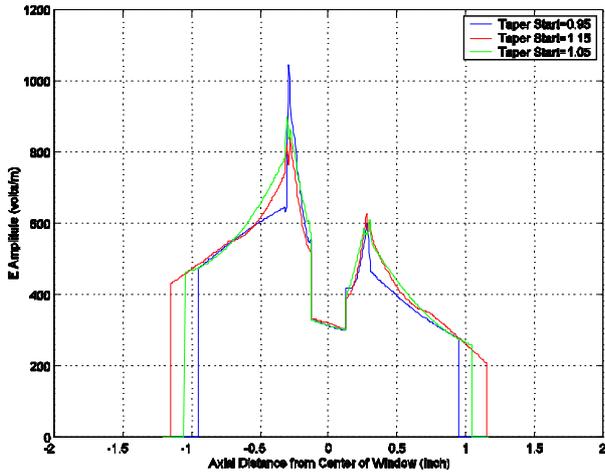


Figure 2: AMAC-1 Electric Field Amplitude along Inner Conductor Surface.

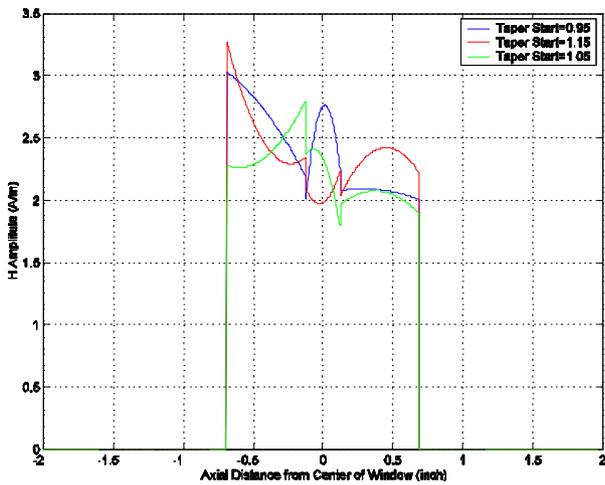


Figure 3: Magnetic Field Amplitude along the Inner Conductor Surface.

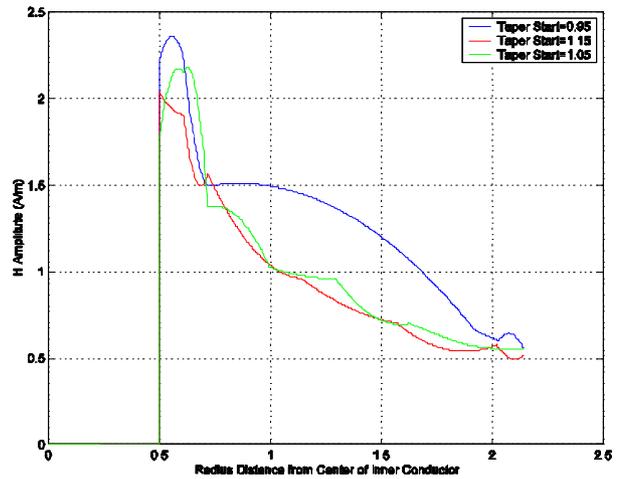


Figure 4: Magnetic Field Amplitude along the Ceramic Window Surface.

Figures 5 and 6 show the MAFIA calculation results for the electric and magnetic fields for 0.5 W incident power. Figure 7 is a contour plot of the dielectric loss in the ceramic. Figures 8(a) and 8(b) show the dielectric loss distribution, and the electric fields at the center plane of the ceramic for 1W incident power.

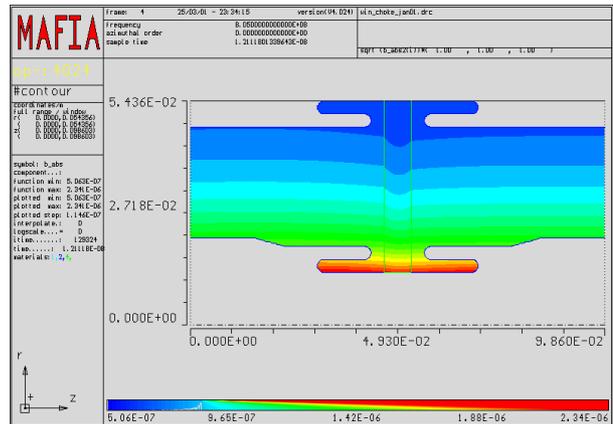


Figure 5: Contour plot of magnetic field in AMAC-1 at 1/2W incident power.

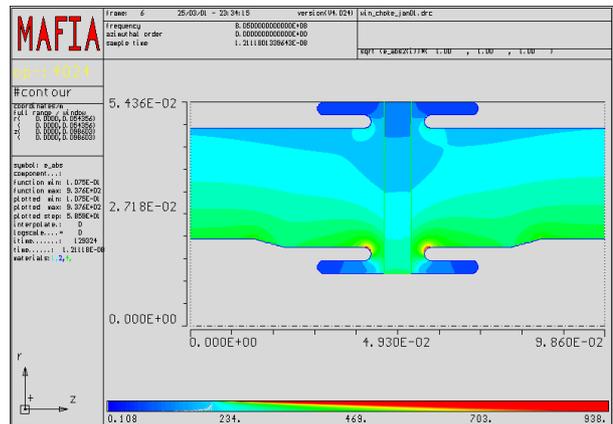


Figure 6: Contour plot of electric field in AMAC-1 at 1/2W incident power.

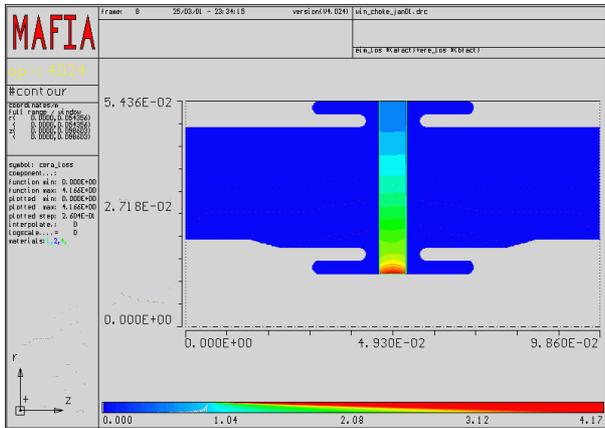


Figure 7: Contour plot of AMAC-1 dielectric losses in the ceramic at 1/2W incident power.

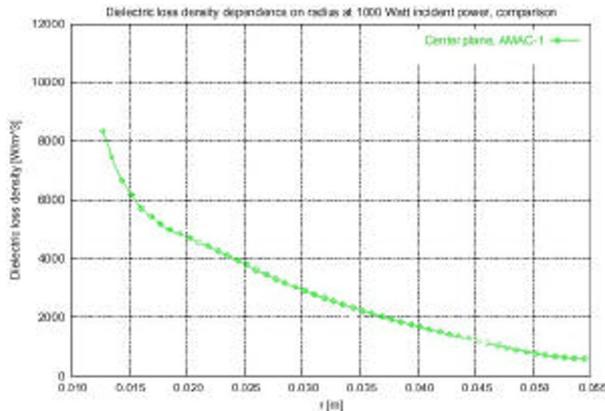


Figure 8a: Radius dependence of dielectric loss at 1000 W incident power for AMAC -1.

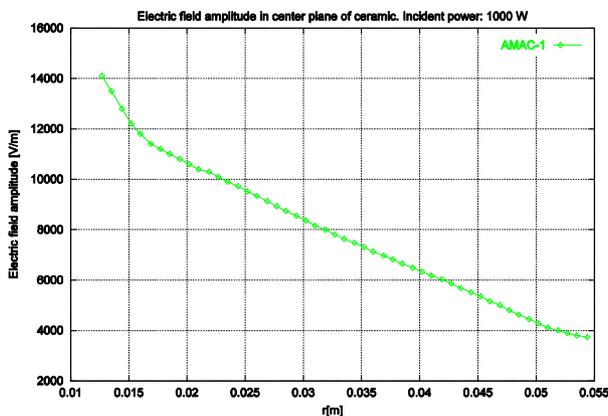


Figure 8b: Radius dependence of electric field at the ceramic center plane of AMAC -1 at 1000 W of incident power.

MULTIPACTING CALCULATION RESULTS

Secondary electron emission data for copper extended to 50eV on the lower energy side was used in the

calculations for all copper and copper plated surfaces for the SNS design and apply also to the RIA coupler. The secondary electron emission values for TiN were used for the ceramic window surface.

The calculations were performed at the University of Helsinki with a specially developed program which tracks electron trajectories in various wave reflection conditions and determines their enhancement possibility for different power levels.

These calculations are considered a reliable indication of multipacting occurring due to secondary electron emission on the coupler surfaces in the vacuum region, and are used to validate the coupler geometry in the design stage.

The description and results of the calculations are shown in more detail in another paper [1]

RF TEST RESULTS

The external Q was measured with the cavity as shown in Fig. 9. The coupler windows have been conditioned and successfully RF tested at the Jefferson Laboratory to meet the RIA specifications. All results met or exceeded the specified values and only a mild temperature increase of the window was measured during long periods at full power RF. A separate presentation at this workshop [2] shows the detail test results.

Electron activity (about 20 nA) started to manifest at one coupler during constant RF power tests at 12 kW RF power (20% higher power level than maximum design value).

No bias voltage was applied during all these tests.

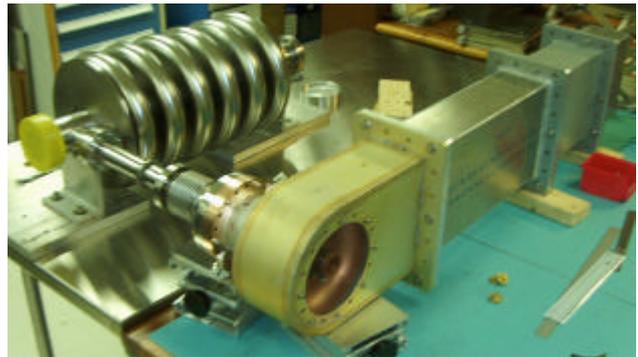


Figure 9: RIA Coupler mounted on SRF Cavity.

REFERENCES

- [1] Q.S.Shu, J.Susta, G.Cheng (AMAC), S.Einarson, T.A.Treado, W.C.Guss, M.Tracy (CPI) "Design and Fabrication of Input RF Coupler Windows for the SNS", High Power Coupler Workshop, Newport News, USA, 2002.
- [2] M. Stirbet, T.L. Grimm, J. Popielarski and M..Johnson, "RF conditioning and testing of fundamental power couplers for the RIA project", this workshop.